

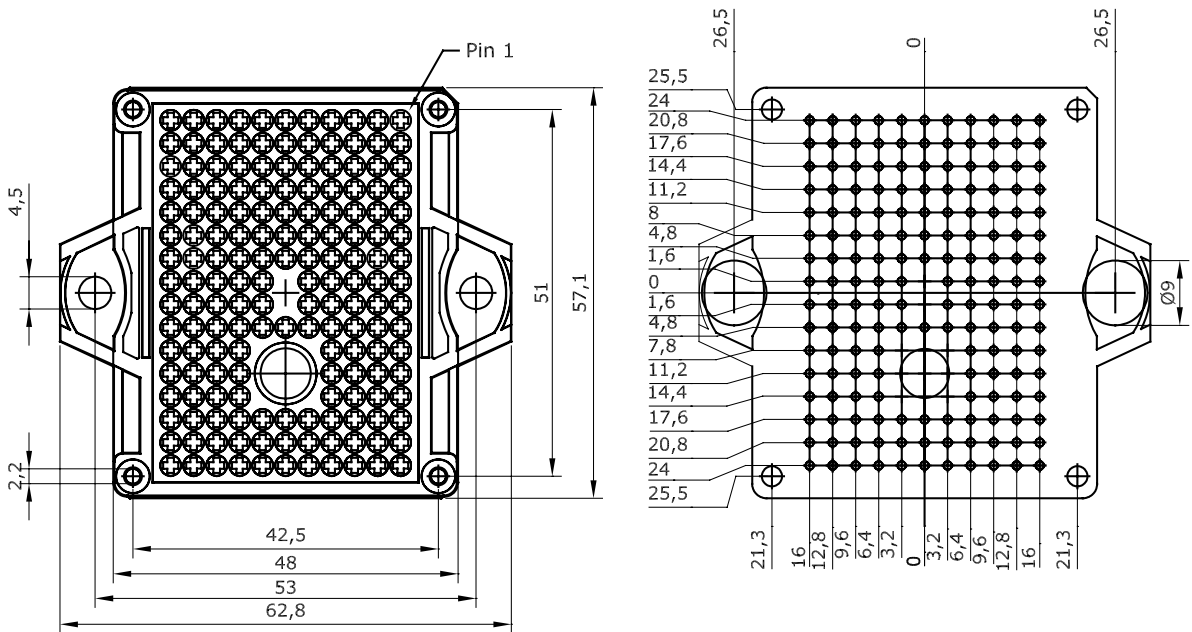
SiC Modules / Full SiC / Semitop E1/E2

Type	V_{DS} V	I_D @ $T_c = 25^\circ\text{C}$ A	$R_{DS(on)}$ @ $T_j = 25^\circ\text{C}$ typ. mΩ	$R_{th(j-a)}$ K/W	Case	Circuit
1200V - SiC MOSFET						
SK200MB120TSCE2 ¹⁾	1200	400	3.7	0.4	E2	

Footnotes: 1) Sample status

Cases

SEMITOP E2



Dimensions in mm

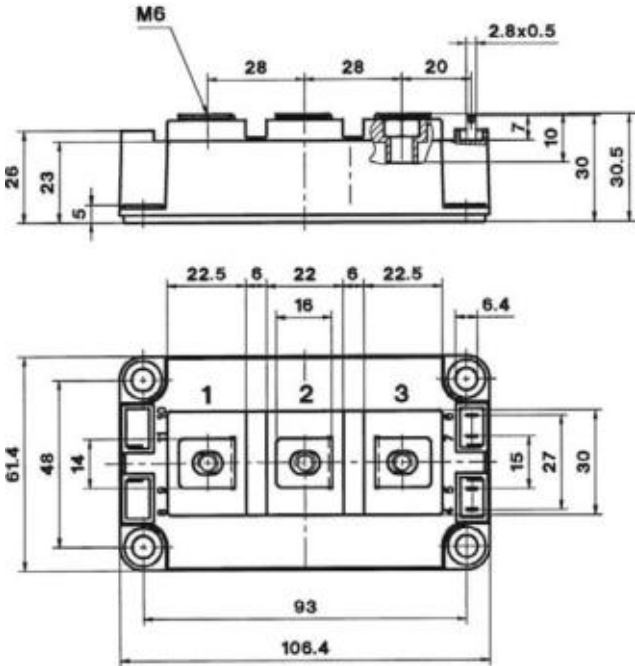
SiC Modules / Full SiC / SEMITRANS

Type	V_{DS} V	I_D @ $T_c = 25^\circ\text{C}$ A	$R_{DS(on)}$ @ $T_j = 25^\circ\text{C}$ typ. mΩ	$R_{th(j-a)}$ K/W	Case	Circuit
1200V - SiC MOSFET						
SKM350MB120SCH15 ¹⁾	1200	523	5.6	0.05	3	
SKM500MB120SC ¹⁾	1200	541	3.8	0.07	3	
SKM350MB120SCH17 ¹⁾	1200	523	5.6	0.045	3	

Footnotes: 1) Sample status

Cases

SEMISTRANS 3



Dimensions in mm